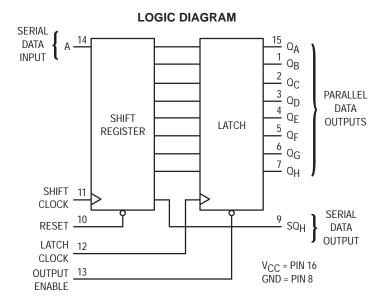
8-Bit Serial-Input/Serial or Parallel-Output Shift Register with Latched 3-State Outputs

High-Performance Silicon-Gate CMOS

The MC74HC595A consists of an 8-bit shift register and an 8-bit D-type latch with three-state parallel outputs. The shift register accepts serial data and provides a serial output. The shift register also provides parallel data to the 8-bit latch. The shift register and latch have independent clock inputs. This device also has an asynchronous reset for the shift register.

The HC595A directly interfaces with the SPI serial data port on CMOS MPUs and MCUs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 328 FETs or 82 Equivalent Gates
- Improvements over HC595
 - Improved Propagation Delays
 - 50% Lower Quiescent Power
 - Improved Input Noise and Latchup Immunity





http://onsemi.com

MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648 MC74HC595AN

AWLYYWW

1



SO-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



A = Assembly Location

WL = Wafer Lot

YY = Year

WW = Work Week

PIN ASSIGNMENT

			_
Q _B [1 ●	16	v _{cc}
OC [2	15	<u>ο</u> Α
QD [3	14	þ A
Q _E [4	13	OUTPUT ENABLE
Q _F [5	12	LATCH CLOCK
Q _G [6	11	SHIFT CLOCK
Q _H [7	10	RESET
GND [8	9	so _H

ORDERING INFORMATION

Device	Package	Shipping
MC74HC595AN	PDIP-16	2000 / Box
MC74HC595AD	SOIC-16	48 / Rail
MC74HC595ADR2	SOIC-16	2500 / Reel
MC74HC595ADT	TSSOP-16	96 / Rail
MC74HC595ADTR2	TSSOP-16	2500 / Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
Vcc	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 35	mA
ICC	DC Supply Current, V _{CC} and GND Pins	± 75	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
VCC	DC Supply Voltage (Referenced to GI	ND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	٧	
TA	Operating Temperature, All Package	Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	Guaranteed Limit		
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
VOH	Minimum High-Level Output Voltage, Q _A - Q _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V_{in} = V_{IH} or V_{IL} $ I_{out} \le 2.4$ mA $ I_{out} \le 6.0$ mA $ I_{out} \le 7.8$ mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
VOL	Maximum Low–Level Output Voltage, Q _A – Q _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V_{in} = V_{IH} or V_{IL} $ I_{out} \le 2.4$ mA $ I_{out} \le 6.0$ mA $ I_{out} \le 7.8$ mA	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	

^{*}Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VOH	Minimum High-Level Output Voltage, SQH	$V_{in} = V_{IH} \text{ or } V_{IL}$ $II_{out}I \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} I_{\text{Out}} \leq 2.4 \text{ mA} \ I_{\text{Out}} \leq 4.0 \text{ mA} \ I_{\text{Out}} \leq 5.2 \text{ mA}$	3.0 4.5 6.0	2.98 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V _{OL}	Maximum Low-Level Output Voltage, SQH	$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $II_{\text{Out}}I \leq 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{aligned} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & I_{\text{Out}} \leq 2.4 \text{ mA} \\ & I_{\text{Out}} \leq 4.0 \text{ mA} \\ & I_{\text{Out}} \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
lin	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μА
loz	Maximum Three–State Leakage Current, Q _A – Q _H	Output in High-Impedance State Vin = VIL or VIH Vout = VCC or GND	6.0	± 0.5	± 5.0	± 10	μА
lcc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μА

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

		Gu	aranteed Li	mit		
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 7)	2.0 3.0 4.5 6.0	6.0 15 30 35	4.8 10 24 28	4.0 8.0 20 24	MHz
^t PLH [,] ^t PHL	Maximum Propagation Delay, Shift Clock to SQ _H (Figures 1 and 7)	2.0 3.0 4.5 6.0	140 100 28 24	175 125 35 30	210 150 42 36	ns
^t PHL	Maximum Propagation Delay, Reset to SQ _H (Figures 2 and 7)	2.0 3.0 4.5 6.0	145 100 29 25	180 125 36 31	220 150 44 38	ns
^t PLH [,] ^t PHL	Maximum Propagation Delay, Latch Clock to Q _A – Q _H (Figures 3 and 7)	2.0 3.0 4.5 6.0	140 100 28 24	175 125 35 30	210 150 42 36	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q _A – Q _H (Figures 4 and 8)	2.0 3.0 4.5 6.0	150 100 30 26	190 125 38 33	225 150 45 38	ns
^t PZL [,] ^t PZH	Maximum Propagation Delay, Output Enable to Q _A – Q _H (Figures 4 and 8)	2.0 3.0 4.5 6.0	135 90 27 23	170 110 34 29	205 130 41 35	ns
tTLH, tTHL	Maximum Output Transition Time, Q _A – Q _H (Figures 3 and 7)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 31 18 15	ns

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

			Gu			
Symbol	Parameter	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{TLH} , t _{THL}	Maximum Output Transition Time, SQ _H (Figures 1 and 7)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State), Q _A – Q _H	_	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Package)*	300	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_f = t_f = 6.0 \text{ ns}$)

			Gu			
Symbol	Parameter	V _{CC}	25°C to - 55°C	≤ 85°C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, Serial Data Input A to Shift Clock (Figure 5)	2.0 3.0 4.5 6.0	50 40 10 9.0	65 50 13 11	75 60 15 13	ns
t _{su}	Minimum Setup Time, Shift Clock to Latch Clock (Figure 6)	2.0 3.0 4.5 6.0	75 60 15 13	95 70 19 16	110 80 22 19	ns
^t h	Minimum Hold Time, Shift Clock to Serial Data Input A (Figure 5)	2.0 3.0 4.5 6.0	5.0 5.0 5.0 5.0	5.0 5.0 5.0 5.0	5.0 5.0 5.0 5.0	ns
^t rec	Minimum Recovery Time, Reset Inactive to Shift Clock (Figure 2)	2.0 3.0 4.5 6.0	50 40 10 9.0	65 50 13 11	75 60 15 13	ns
t _W	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	60 45 12 10	75 60 15 13	90 70 18 15	ns
t _W	Minimum Pulse Width, Shift Clock (Figure 1)	2.0 3.0 4.5 6.0	50 40 10 9.0	65 50 13 11	75 60 15 13	ns
t _W	Minimum Pulse Width, Latch Clock (Figure 6)	2.0 3.0 4.5 6.0	50 40 10 9.0	65 50 13 11	75 60 15 13	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

FUNCTION TABLE

			Inputs			Resulting Function				
Operation	Reset	Serial Input A	Shift Clock	Latch Clock	Output Enable	Shift Register Contents	Latch Register Contents	Serial Output SQ _H	Parallel Outputs Q _A – Q _H	
Reset shift register	L	Х	Х	L, H, ↓	L	L	U	L	U	
Shift data into shift register	Н	D	1	L, H, ↓	L	D SR _A ; SR _N SR _{N+1}	U	SR _G SR _H	U	
Shift register remains unchanged	Н	Х	L, H, ↓	L, H, ↓	L	U	U	U	U	
Transfer shift register contents to latch register	Н	Х	L, H, ↓	1	L	U	SR _N LR _N	U	SR _N	
Latch register remains unchanged	Х	Х	Х	L, H, ↓	L	*	U	*	U	
Enable parallel outputs	Х	Х	Х	Х	L	*	**	*	Enabled	
Force outputs into high impedance state	Х	Х	Х	Х	Н	*	**	*	Z	

SR = shift register contents LR = latch register contents D = data (L, H) logic level U = remains unchanged \uparrow = Low-to-High \downarrow = High-to-Low

* = depends on Reset and Shift Clock inputs

** = depends on Latch Clock input

PIN DESCRIPTIONS

INPUTS A (Pin 14)

Serial Data Input. The data on this pin is shifted into the 8-bit serial shift register.

CONTROL INPUTS Shift Clock (Pin 11)

Shift Register Clock Input. A low–to–high transition on this input causes the data at the Serial Input pin to be shifted into the 8–bit shift register.

Reset (Pin 10)

Active—low, Asynchronous, Shift Register Reset Input. A low on this pin resets the shift register portion of this device only. The 8—bit latch is not affected.

Latch Clock (Pin 12)

Storage Latch Clock Input. A low-to-high transition on this input latches the shift register data.

Output Enable (Pin 13)

Active—low Output Enable. A low on this input allows the data from the latches to be presented at the outputs. A high on this input forces the outputs (QA-QH) into the high-impedance state. The serial output is not affected by this control unit.

OUTPUTS

Q_A - Q_H (Pins 15, 1, 2, 3, 4, 5, 6, 7)

Noninverted, 3-state, latch outputs.

SQ_H (Pin 9)

Noninverted, Serial Data Output. This is the output of the eighth stage of the 8-bit shift register. This output does not have three-state capability.

SWITCHING WAVEFORMS

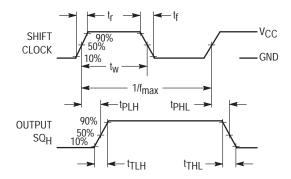


Figure 1.

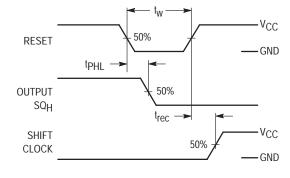


Figure 2.

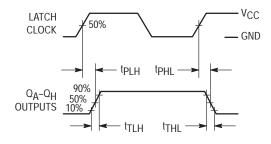


Figure 3.

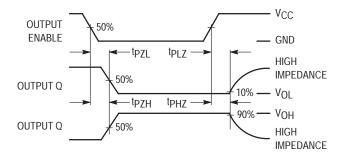


Figure 4.

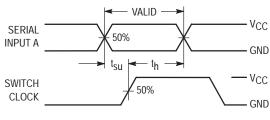


Figure 5.

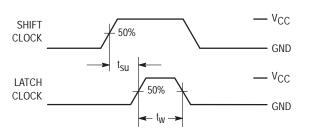
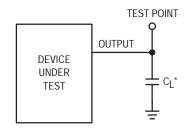


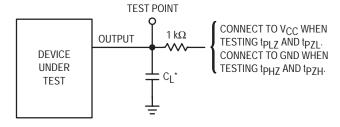
Figure 6.

TEST CIRCUITS



*Includes all probe and jig capacitance

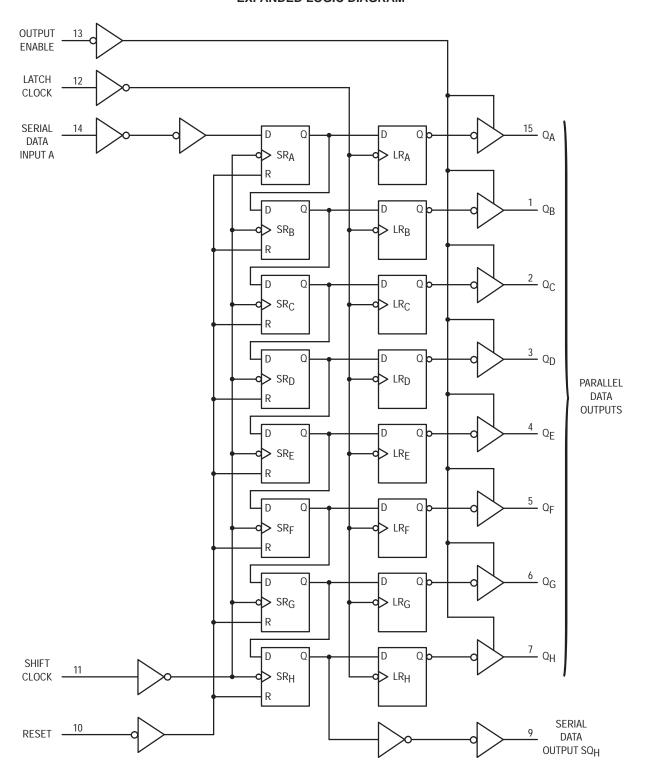
Figure 7.



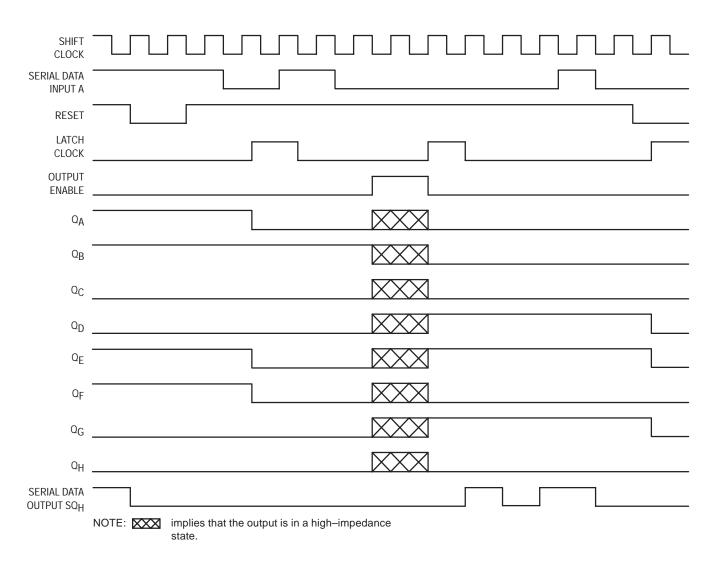
*Includes all probe and jig capacitance

Figure 8.

EXPANDED LOGIC DIAGRAM

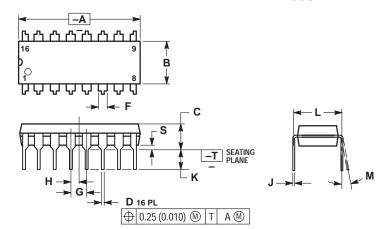


TIMING DIAGRAM



PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 ISSUE R



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.
- Y14.5M, 1982.

 CONTROLLING DIMENSION: INCH.

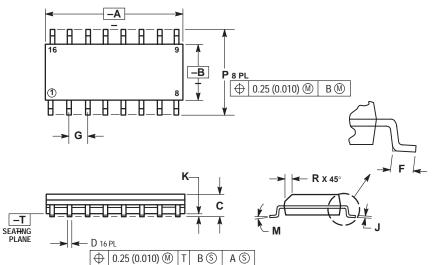
 DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

 DIMENSION B DOES NOT INCLUDE MOLD FLASH.

 ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.	100 BSC	2	.54 BSC
Н	0.	050 BSC	1	.27 BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01





NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

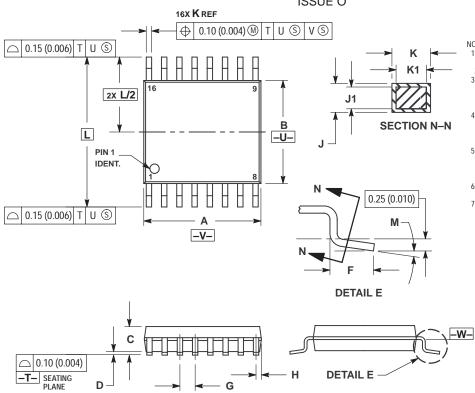
 5. DIMENSION DIDDES NOT INCLUDE SAMMAD.

- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE O**



NOTES:

- OTES.
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH.
 PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR
- PROTRUSION SHALL NOT EXCEED

 0.25 (0.010) PER SIDE.

 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION
 SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8°	0°	8°

Notes

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